National Semiconductor

January 1988

MM54HCT04/MM74HCT04 Hex Inverter

General Description

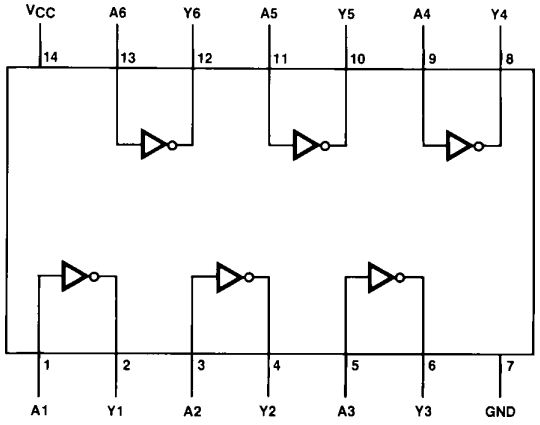
The MM54HCT04/MM74HCT04 are logic functions fabricated by using advanced silicon-gate CMOS technology which provides the inherent benefits of CMOS - low quiescent power and wide power supply range. These devices are input and output characteristic as well as pin-out compatible with standard DM54LS/74LS logic families. The MM54HCT04/MM74HCT04, triple buffered, hex inverters, feature low power dissipation and fast switching times. All inputs are protected from static discharge by internal diodes to V_{CC} and ground.

MM54HCT/MM74HCT devices are intended to interface between TTL and NMOS components and standard CMOS devices. These parts are also plug-in replacements for LS-TTL devices and can be used to reduce power consumption in existing designs.

Features

- TTL, LS pin-out and threshold compatible
- Fast switching: t_{PLH}, t_{PHL} = 12 ns (typ)
- Low power: 10 μW at DC, 3.7 mW at 5 MHz
- High fanout: $\geq$ 10 LS loads
- Inverting, triple buffered

Connection Diagram



TL/F/5357–1

Top View

Order Number MM54HCT04 or MM74HCT04

RRD-B30M105/Printed in U. S. A.

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to V_{CC} +1.5V
DC Output Voltage (V_{OUT})	−0.5 to V_{CC} +0.5V
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±50 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. (T_L) (Soldering 10 seconds)	260°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	4.5	5.5	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (T_A)			
MM74HCT	−40	+85	°C
MM54HCT	−55	+125	°C
Input Rise or Fall Times (t_r, t_f)		500	ns

DC Electrical Characteristics V_{CC} = 5V ±10% (unless otherwise specified)

Symbol	Parameter	Conditions	T_A = 25°C	74HCT T_A = −40 to 85°C	54HCT T_A = −55 to 125°C	Units
			Typ	Guaranteed Limits		
V_{IH}	Minimum High Level Input Voltage			2.0	2.0	2.0	V
V_{IL}	Maximum Low Level Input Voltage			0.8	0.8	0.8	V
V_{OH}	Minimum High Level Output Voltage	V_{IN} = V_{IL}					
		$\|I_{OUT}\|$ = 20 μA	V_{CC}	V_{CC} −0.1	V_{CC} −0.1	V_{CC} −0.1	V
		$\|I_{OUT}\|$ = 4.0 mA, V_{CC} = 4.5V	4.2	3.98	3.84	3.7	V
		$\|I_{OUT}\|$ = 4.8 mA, V_{CC} = 5.5V	5.2	4.98	4.84	4.7	V
V_{OL}	Maximum Low Level Voltage	V_{IN} = V_{IH}					
		$\|I_{OUT}\|$ = 20 μA	0	0.1	0.1	0.1	V
		$\|I_{OUT}\|$ = 4.0 mA, V_{CC} = 4.5V	0.2	0.26	0.33	0.4	V
		$\|I_{OUT}\|$ = 4.8 mA, V_{CC} = 5.5V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	V_{IN} = V_{CC} or GND, V_{IH} or V_{IL}		±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND I_{OUT} = 0 μA		2.0	20	40	μA
		V_{IN} = 2.4V or 0.5V (Note 4)		0.3	0.4	0.5	mA

AC Electrical Characteristics V_{CC} = 5.0V, t_r = t_f = 6 ns C_L = 15 pF, T_A = 25°C (unless otherwise noted)

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PLH}, t_{PHL}	Maximum Propagation Delay		10	18	ns

AC Electrical Characteristics V_{CC} = 5.0V ±10%, t_r = t_f = 6 ns, C_L = 50 pF (unless otherwise noted)

Symbol	Parameter	Conditions	T_A = 25°C	74HCT T_A = −40 to 85°C		54HCT T_A = −55 to 125°C	Units
			Typ	Guaranteed Limits			
t_{PLH}, t_{PHL}	Maximum Propagation Delay		14	20	25	30	ns
t_{THL}, t_{TLH}	Maximum Output Rise & Fall Time		8	15	19	22	ns
C_{PD}	Power Dissipation Capacitance	(Note 5)	20				pF
C_{IN}	Input Capacitance		5	10	10	10	pF

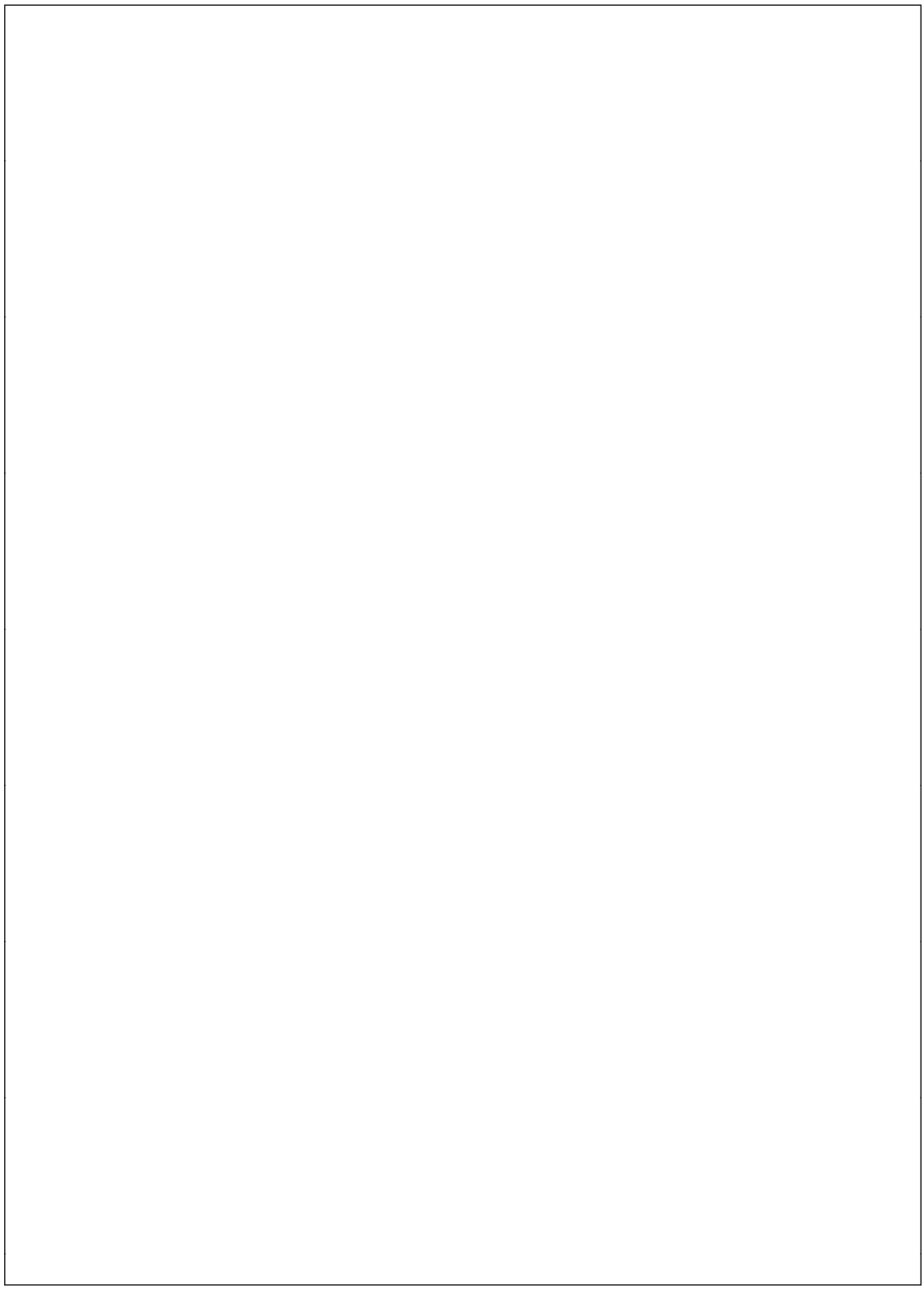
Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

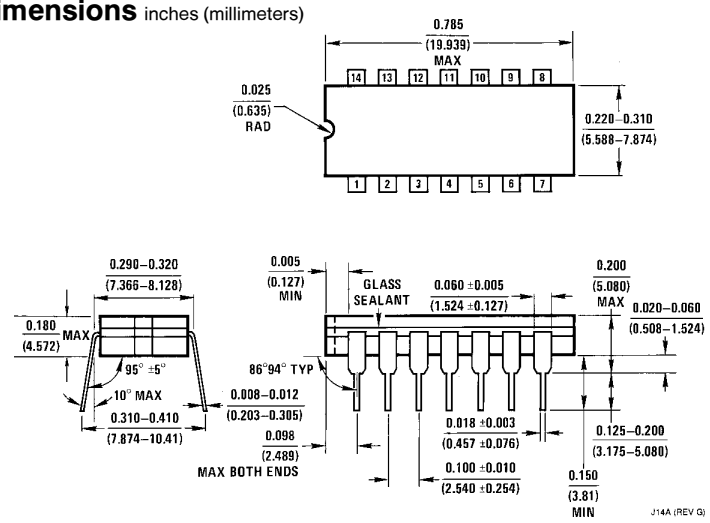
Note 3: Power Dissipation temperature derating — plastic "N" package: −12 mW/°C from 65°C to 85°C; ceramic "J" package: −12 mW/°C from 100°C to 125°C.

Note 4: This is measured per input with all other inputs held at V_{CC} or ground.

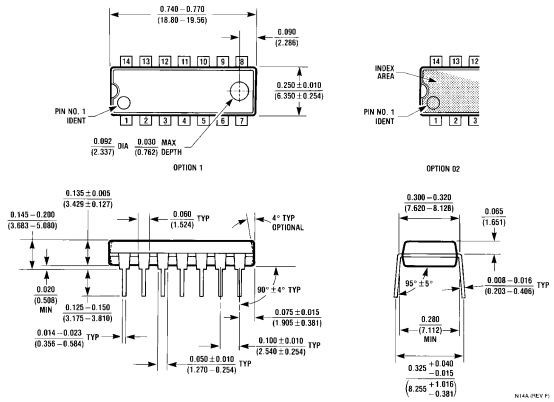
Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.



Physical Dimensions inches (millimeters)



Ceramic Dual-In-Line Package (J)
Order Number MM54HCT04J or MM74HCT04J
NS Package J14A



Molded Dual-In-Line Package (N)
Order Number MM74HCT04N
NS Package N14A

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

National Semiconductor Corporation
1111 West Bardin Road
Arlington, TX 76017
Tel: 1(800) 272-9959
Fax: 1(800) 737-7018

National Semiconductor Europe
Fax: (+49) 0-180-530 85 86
Email: cnjwge@tevm2.nsc.com
Deutsch Tel: (+49) 0-180-530 85 85
English Tel: (+49) 0-180-532 78 32
Français Tel: (+49) 0-180-532 93 58
Italiano Tel: (+49) 0-180-534 16 80

National Semiconductor Hong Kong Ltd.
13th Floor, Straight Block,
Ocean Centre, 5 Canton Rd.
Tsimshatsui, Kowloon
Hong Kong
Tel: (852) 2737-1600
Fax: (852) 2736-9960

National Semiconductor Japan Ltd.
Tel: 81-043-299-2309
Fax: 81-043-299-2408